



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ C$
60V	$5\Omega @ V_{GS} = 10V$	0.15A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package

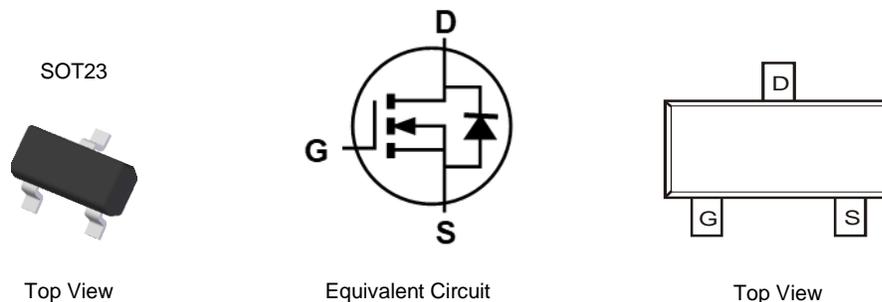
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 ^{e3}
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Continuous Drain Current at T _A = +25°C	I _D	0.15	A
Pulsed Drain Current	I _{DM}	3	A
Gate Source Voltage	V _{GS}	±20	V
Power Dissipation at T _A = +25°C	P _{TOT}	330	mW
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

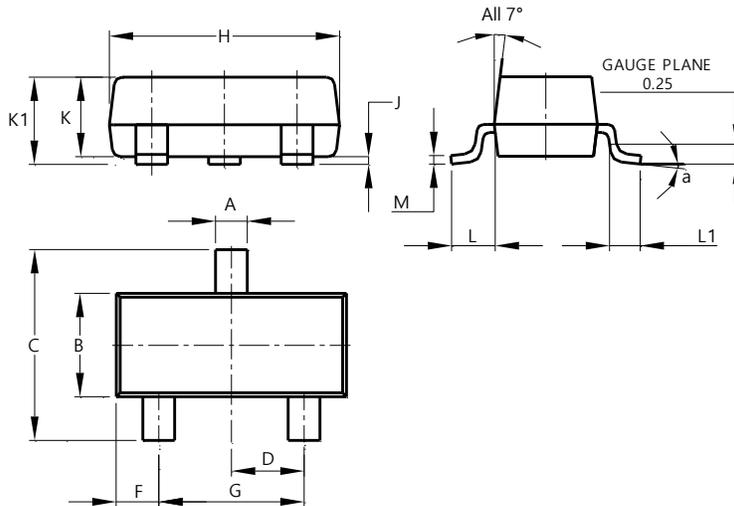
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Drain-Source Breakdown Voltage	BV _{DSS}	60	90	—	V	I _D = 100μA, V _{GS} = 0V
Gate-Source Threshold Voltage	V _{GS(TH)}	0.8	—	3	V	I _D = 1mA, V _{DS} = V _{GS}
Gate-Body Leakage	I _{GSS}	—	—	10	nA	V _{GS} = 15V, V _{DS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 25V, V _{GS} = 0V
Static Drain-Source On-State Resistance	R _{D(S)ON}	—	—	5	Ω	V _{GS} = 10V, I _D = 200mA
Forward Transconductance (Note 5) (Note 6)	g _{fs}	—	200	—	ms	V _{DS} = 10V, I _D = 200mA
Input Capacitance (Note 6)	C _{iss}	—	60	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Turn-On Delay Time (Note 6) (Note 7)	t _{D(ON)}	—	—	10	ns	V _{DD} ≈ -15V, I _D = 600mA
Turn-Off Delay Time (Note 6) (Note 7)	t _{D(OFF)}	—	—	10	ns	

- Notes:
5. Measured under pulsed conditions. Width = 300μs. Duty cycle ≤ 2%.
 6. Sample test.
 7. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.
Spice parameter data is available upon request for this device.
For typical characteristics graphs refer to ZVN3306F datasheet.

Package Outline Dimensions

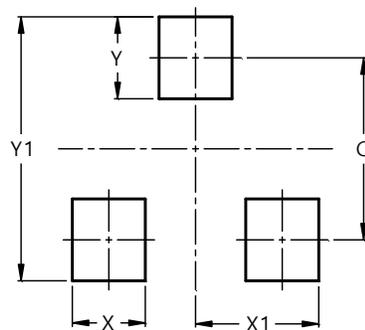
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9